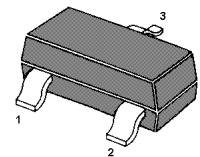


MMBTSC2412

NPN Silicon Epitaxial Planar Transistor
for general purpose applications.

The transistor is subdivided into three groups Q, R and S. according to its DC current gain.



1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	7	V
Collector Current	I_C	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{Stg}	-55 to +150	$^{\circ}\text{C}$

MMBTSC2412

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=6\text{V}$, $I_C=1\text{mA}$	Q h_{FE}	120	-	270	-
	R h_{FE}	180	-	390	-
	S h_{FE}	270	-	560	-
Collector Base Breakdown Voltage at $I_C=50\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C=1\text{mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E=50\mu\text{A}$	$V_{(BR)EBO}$	7	-	-	V
Collector Cutoff Current at $V_{CB}=60\text{V}$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB}=7\text{V}$	I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage at $I_C=50\text{mA}$, $I_B=5\text{mA}$	$V_{CE(sat)}$	-	-	0.4	V
Gain Bandwidth Product at $V_{CE}=12\text{V}$, $-I_E=2\text{mA}$, $f=100\text{MHz}$	f_T	-	180	-	MHz
Output Capacitance at $V_{CE}=12\text{V}$, $f=1\text{MHz}$	C_{OB}	-	2	3.5	pF

Fig. 1 Grounded emitter propagation characteristics

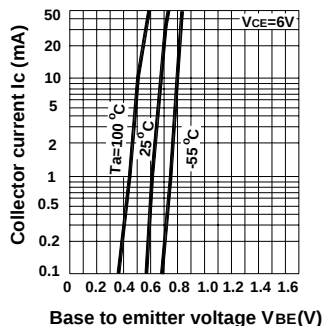


Fig.2 Grounded emitter output characteristics(I)

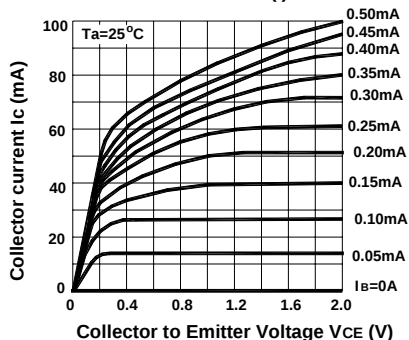


Fig.3 Grounded emitter output characteristics(II)

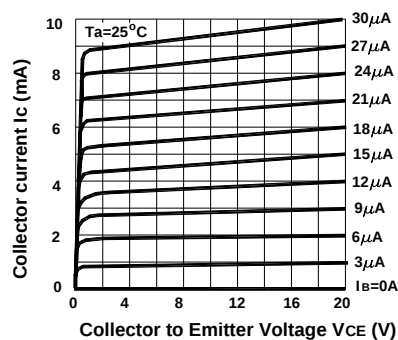


Fig.4 DC current gain vs. collector current (I)

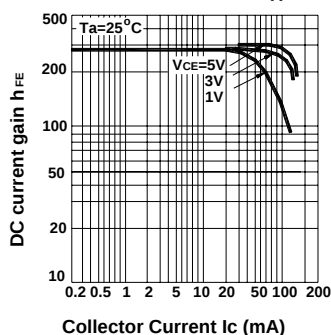


Fig.5 DC current gain vs. collector current (II)

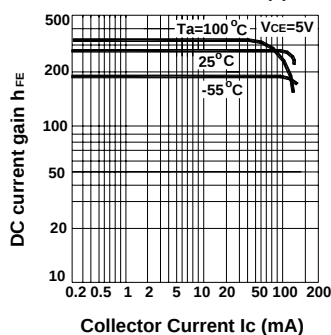


Fig.6 Collector-emitter saturation voltage vs. collector current

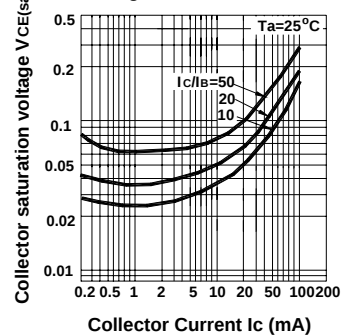


Fig.7 Collector-emitter saturation voltage vs. collector current(I)

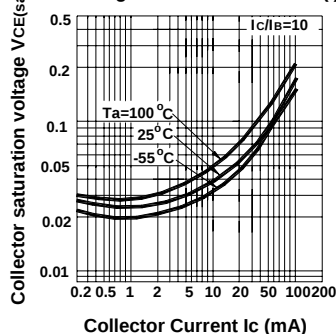


Fig.8 Collector-emitter saturation voltage vs. collector current(II)

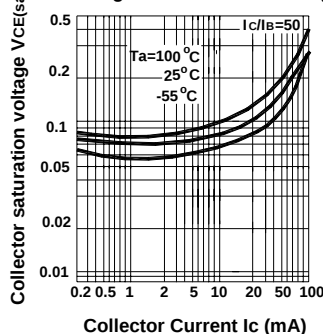


Fig.9 Gain bandwidth product vs. emitter current

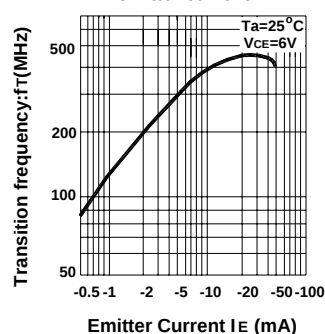


Fig.10 Collector output capacitance vs. collector-base voltage

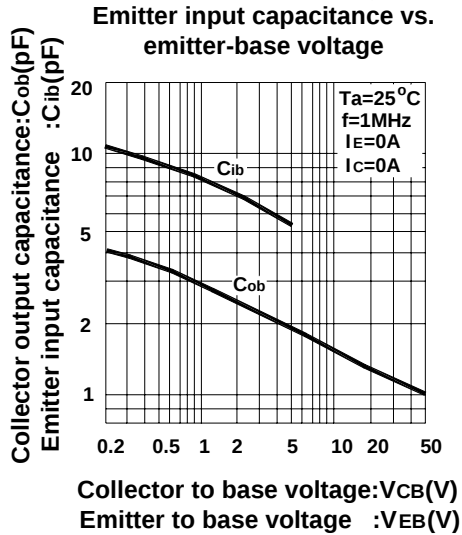


Fig.11 Base-collector time constant vs. emitter current

